Qiang Li

List of Publications by Year in descending order

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35	1,247	304368	414034
papers	citations	22 h-index	32 g-index

35	35	35	829
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	13â€‰â€‰Î¼m submilliamp threshold quantum dot micro-lasers on Si. Optica, 2017, 4, 940.	4.8	142
2	Growing antiphase-domain-free GaAs thin films out of highly ordered planar nanowire arrays on exact (001) silicon. Applied Physics Letters, 2015, 106, .	1.5	135
3	Optically pumped 13â€‰â€‰Î¼m room-temperature InAs quantum-dot micro-disk lasers directly grown on (001) silicon. Optics Letters, 2016, 41, 1664.	1.7	101
4	Monolithically integrated InAs/InGaAs quantum dot photodetectors on silicon substrates. Optics Express, 2017, 25, 27715.	1.7	71
5	Sub-wavelength InAs quantum dot micro-disk lasers epitaxially grown on exact Si (001) substrates. Applied Physics Letters, 2016, 108, .	1.5	58
6	Continuous-Wave Optically Pumped 1.55 Î¼m InAs/InAlGaAs Quantum Dot Microdisk Lasers Epitaxially Grown on Silicon. ACS Photonics, 2017, 4, 204-210.	3.2	56
7	1.55â€‰Î¼m room-temperature lasing from subwavelength quantum-dot microdisks directly grown on (001) Si. Applied Physics Letters, 2017, 110, .	1.5	50
8	1.5 Î¼m quantum-dot diode lasers directly grown on CMOS-standard (001) silicon. Applied Physics Letters, 2018, 113, .	1.5	50
9	Low Dark Current High Gain InAs Quantum Dot Avalanche Photodiodes Monolithically Grown on Si. ACS Photonics, 2020, 7, 528-533.	3.2	49
10	Telecom InP/InGaAs nanolaser array directly grown on (001) silicon-on-insulator. Optics Letters, 2019, 44, 767.	1.7	45
11	Room-temperature InP/InGaAs nano-ridge lasers grown on Si and emitting at telecom bands. Optica, 2018, 5, 918.	4.8	40
12	Room-temperature electrically-pumped 15 Î¼m InGaAs/InAlGaAs laser monolithically grown on on-axis (001) Si. Optics Express, 2018, 26, 14514.	1.7	35
13	1.55-Î¼m Lasers Epitaxially Grown on Silicon. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-11.	1.9	35
14	Growing InGaAs quasi-quantum wires inside semi-rhombic shaped planar InP nanowires on exact (001) silicon. Applied Physics Letters, 2016, 108, 242105.	1.5	33
15	Temperature characteristics of epitaxially grown InAs quantum dot micro-disk lasers on silicon for on-chip light sources. Applied Physics Letters, 2016, 109, .	1.5	31
16	Self-organized InAs/InAlGaAs quantum dots as dislocation filters for InP films on (001) Si. Journal of Crystal Growth, 2017, 464, 28-32.	0.7	31
17	Low Threshold Quantum Dot Lasers Directly Grown on Unpatterned Quasi-Nominal (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-9.	1.9	29
18	InGaAs/InP quantum wires grown on silicon with adjustable emission wavelength at telecom bands. Nanotechnology, 2018, 29, 225601.	1.3	27

#	Article	IF	Citations
19	Defect reduction in epitaxial InP on nanostructured Si (001) substrates with position-controlled seed arrays. Journal of Crystal Growth, 2014, 405, 81-86.	0.7	24
20	Epitaxial growth of high quality InP on Si substrates: The role of InAs/InP quantum dots as effective dislocation filters. Journal of Applied Physics, 2018, 123, .	1.1	24
21	Epitaxial growth of GaSb on V-grooved Si (001) substrates with an ultrathin GaAs stress relaxing layer. Applied Physics Letters, 2017, 111, .	1.5	23
22	Continuous-wave lasing from InP/InGaAs nanoridges at telecommunication wavelengths. Applied Physics Letters, 2017, 111, 212101.	1.5	23
23	Low-Threshold Epitaxially Grown 1.3-Î¼m InAs Quantum Dot Lasers on Patterned (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-7.	1.9	23
24	GaAs-InGaAs-GaAs Fin-Array Tunnel Diodes on (001) Si Substrates With Room-Temperature Peak-to-Valley Current Ratio of 5.4. IEEE Electron Device Letters, 2016, 37, 24-27.	2.2	22
25	Highly ordered horizontal indium gallium arsenide/indium phosphide multi-quantum-well in wire structure on (001) silicon substrates. Journal of Applied Physics, 2016, 120, .	1.1	19
26	Growth of ultra-high mobility In_{0.52}Al_{0.48}As/In_xGa_{1â^'}_xAs (xâ‰¥ 53%) quantum wells on Si substrates using InP/GaAs buffers by metalorganic chemical vapor deposition. Applied Physics Express, 2014, 7, 045502.	1.1	18
27	Parametric study of high-performance 155 Î¼m InAs quantum dot microdisk lasers on Si. Optics Express, 2017, 25, 31281.	1.7	14
28	Chemical vapor deposited monolayer MoS2top-gate MOSFET with atomic-layer-deposited ZrO2as gate dielectric. Semiconductor Science and Technology, 2018, 33, 045004.	1.0	14
29	InAlGaAs/InAlAs MQWs on Si Substrate. IEEE Photonics Technology Letters, 2015, 27, 748-751.	1.3	13
30	Interface passivation and trap reduction via hydrogen fluoride for molybdenum disulfide on silicon oxide back-gate transistors. Semiconductor Science and Technology, 2018, 33, 045005.	1.0	7
31	III-V Superlattices on InP/Si Metamorphic Buffer Layers for Î» â‰ˆ4.8â€‰Î¼m Quantum Cascade Lasers. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800493.	0.8	4
32	Heterointerface study of InAs/GaSb nanoridge heterostructures grown by metal organic chemical vapor deposition on V-grooved Si (0â€¯0â€¯1) substrates. Journal of Crystal Growth, 2018, 484, 12-16.	0.7	1
33	1.5 Î¼m Room-Temperature Electrically Pumped Quantum Dot Lasers Monolithically Grown on Exact (001) Si. , 2018, , .		0
34	Defect characterization of InAs/InGaAs quantum dot photodetector grown on GaAs-on-V-grooved-Si substrate. , 2019, , .		0
35	III-V Lasers Emitting at 1.3 to 1.5 Âµm grown on (001) silicon by MOCVD (invited). , 2019, , .		0